

## Abstract

## Method for the Production of Transistor Structures with LDD

5           The substrate (1) is etched such that on the source side and on the drain side  
downward sloping sidewalls (5) are formed adjacent to the gate electrode (3) and sloping  
downward from it. Spacers (7) are positioned there. An implantation (9) of dopant is  
performed at a low angle relative to the upper surface, through the spacers (7), in order to  
form the regions (11) of lower dopant concentration, and an implantation (10) of dopant is  
10 performed at a high angle relative to the upper surface in order to form the source and  
drain regions (12).

Figure 6